

S1ZB60-7101

Bridge Diodes

600V, 0.8A

Feature

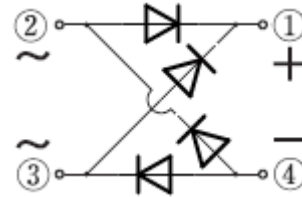
- Small DIP (There is also SMD)
- High Reliability
- Pb free terminal
- RoHS:Yes

OUTLINE

Package (House Name): 1Z



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	T _{stg}		-40 to 150	°C
Junction temperature	T _j		-40 to 150	°C
Repetitive peak reverse voltage	V _{RRM}		600	V
Average forward current	I _{F(AV)}	50Hz sine wave, Resistance load, Tl=117°C	0.8	A
Average forward current	I _{F(AV)}	50Hz sine wave, Resistance load, On alumina substrate, Ta=25°C ※	0.8	A
Average forward current	I _{F(AV)}	50Hz sine wave, Resistance load, On glass-epoxy substrate, Ta=25°C ※	0.5	A
Surge forward current	I _{FSM}	50Hz sine wave, Non-repetitive 1 cycle peak value, T _j =25°C	30	A
Current squared time	I ² t	1ms ≤ tp < 10ms, T _j =25°C, per diode	4.5	A ² s

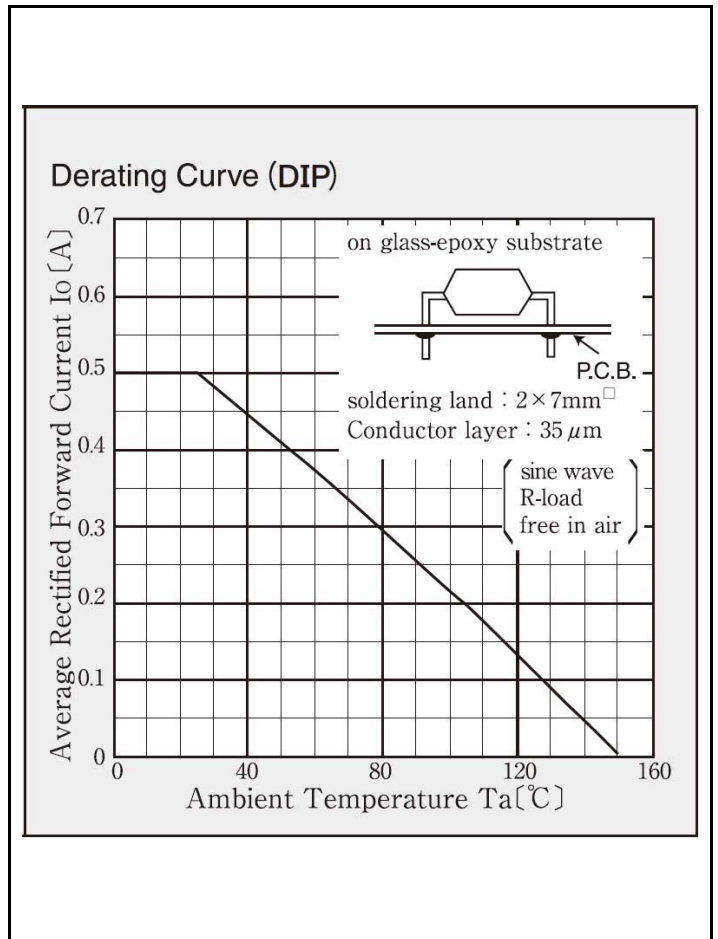
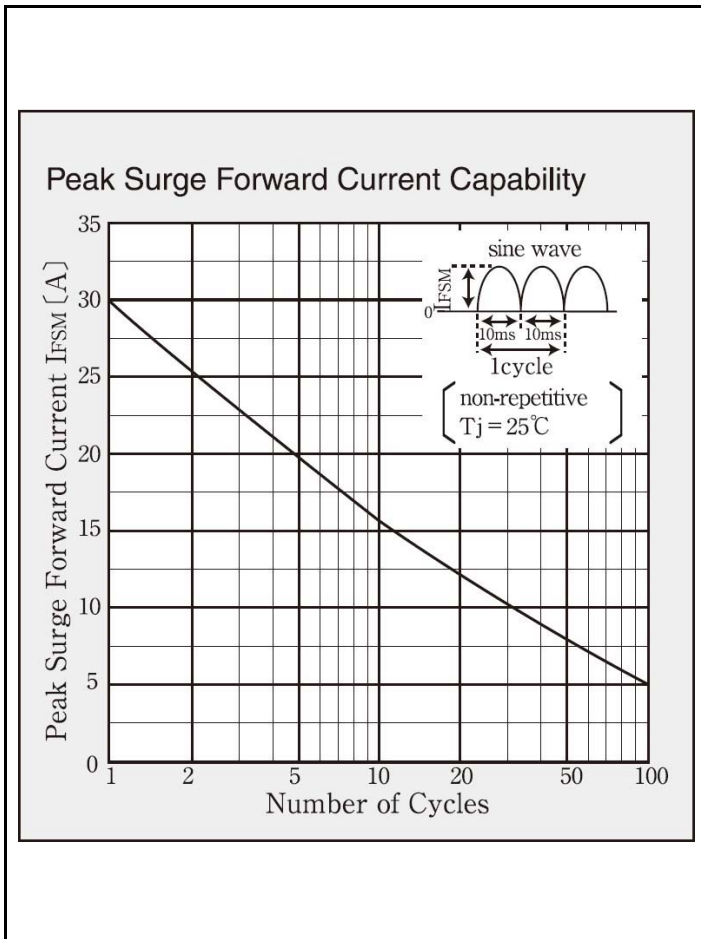
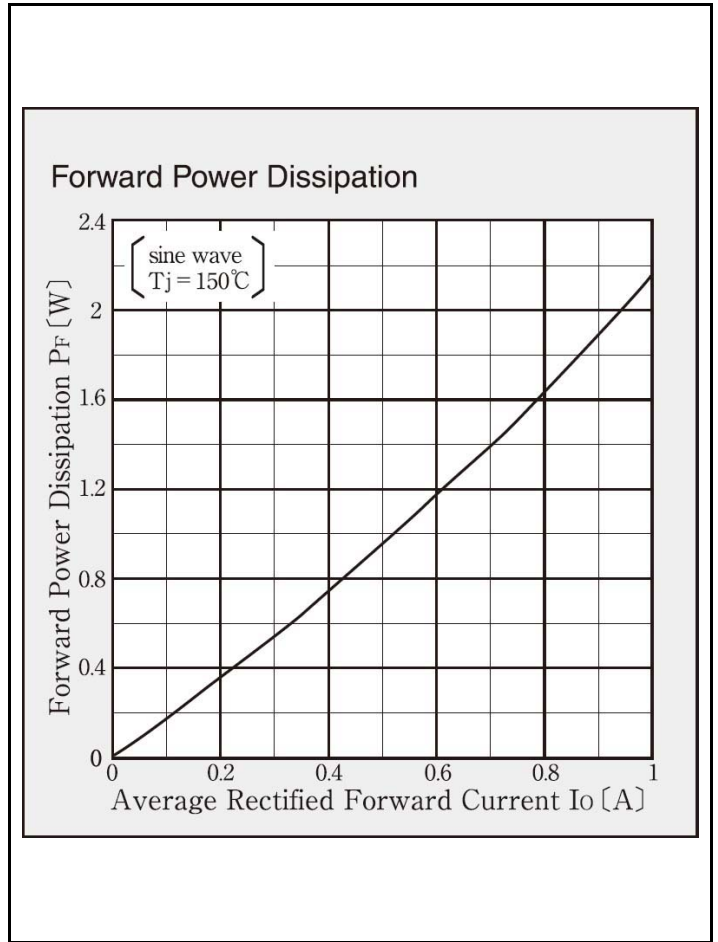
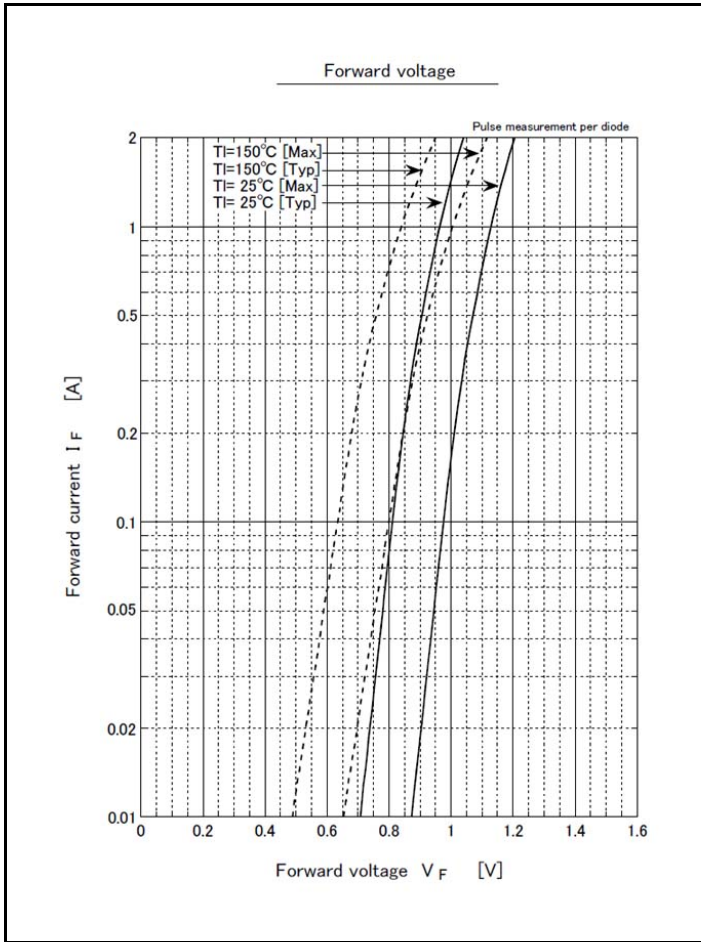
※ : See the original Specifications

Electrical Characteristics (unless otherwise specified : Tl=25°C)

Item	Symbol	Conditions	Ratings			Unit
			MIN	TYP	MAX	
Forward voltage	V_F	$I_F=0.4A$, Pulse measurement, per diode			1.05	V
Reverse current	I_R	$V_R=600V$, Pulse measurement, per diode			10	μA
Thermal resistance	$R_{th(j-l)}$	Junction to lead			20	$^{\circ}C/W$
Thermal resistance	$R_{th(j-a)}$	Junction to ambient, On alumina substrate *			76	$^{\circ}C/W$
Thermal resistance	$R_{th(j-a)}$	Junction to ambient, On glass-epoxy substrate *			134	$^{\circ}C/W$

* :See the original Specifications

CHARACTERISTIC DIAGRAMS



C3

JEDEC Code	—
JEITA Code	—
House Name	1Z(DIP)

